

Appl. No. 10/669,111
Reply to Office action of 12/13/2004

REMARKS

Reconsideration of the above-referenced application in view of the above amendment, and of the following remarks, is respectfully requested.

Claims 1-18 are pending in this case. Claims 1 and 13 are amended herein and claims 19-26 are cancelled herein.

The Examiner rejected claims 1, 2, 4, 5, 7, 9, 10, 13-16, and 17 under 35 U.S.C. 102(e) as being anticipated by Beasom (U.S. Patent 5,650,658).

Applicant respectfully submits that amended claim 1 is unanticipated by Beasom as there is no disclosure or suggestion in Beasom of forming a first well and forming a second well, wherein portions of the first and second wells overlap in a compensated channel region of the substrate and wherein the compensated channel region is located directly adjacent a source and spaced apart from a thick dielectric, as required by claim 1. Beasom teaches a high voltage lateral CMOS device in which an N-well and P-drift region overlap. However, this overlapping region in Beasom is directly adjacent the thick oxide region rather than being directly adjacent a source and spaced apart from the thick dielectric, as required by claim 1. Accordingly, Applicant respectfully submits that claim 1 and the claims dependent thereon are unanticipated by Beasom.

Applicant respectfully submits that amended claim 13 is unanticipated by Beasom as there is no disclosure or suggestion in the reference of forming a compensated channel region extending below a portion of the thin dielectric in the substrate adjacent and physically contacting the source, the compensated channel region comprising dopants of the first and second conductivity types; and forming an adjust region in the substrate proximate the second end of the thick dielectric, the adjust region comprising dopants of the second conductivity type and being spaced apart from the compensated channel region. As discussed above, Beasom teaches a high voltage lateral CMOS device in which an N-well and P-drift region overlap.

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However, this overlapping region in Beasom is directly adjacent the thick oxide region rather than being directly adjacent a source and including an adjust region spaced apart from the compensated channel region. Accordingly, Applicant respectfully submits that claim 13 and the claims dependent thereon are unanticipated by Beasom.

The Examiner rejected claims 3, 6, 8, 11-12 and 18 under 35 U.S.C. 103(a) as being unpatentable over Beasom (U.S. Patent 5,650,658) in further view of Kotecha et al. (U.S. Patent 4,329,186).

Applicant respectfully submits that dependent claims 3, 6, 8, 11, and 12 are patentable over Beasom in view of Kotecha for the same reasons discussed above relative to claim 1, from which these claims depend. Kotecha is added to teach implanting second conductivity type dopants in the adjust region after forming the thick dielectric. There is no disclosure or suggestion in the references as combined of forming a first well and forming a second well, wherein portions of the first and second wells overlap in a compensated channel region of the substrate and wherein the compensated channel region is located directly adjacent a source and spaced apart from a thick dielectric, as required by claim 1.

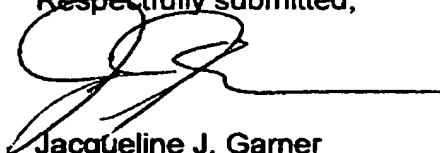
Applicant respectfully submits that dependent claim 18 is patentable over Beasom in view of Kotecha for the same reasons discussed above relative to claim 13, from which this claims depends. Kotecha is added to teach implanting second conductivity type dopants in the adjust region after forming the thick dielectric. There is no disclosure or suggestion in the references of forming a compensated channel region extending below a portion of the thin dielectric in the substrate adjacent and physically contacting the source, the compensated channel region comprising dopants of the first and second conductivity types; and forming an adjust region in the substrate proximate the second end of the thick dielectric, the adjust region comprising dopants of the second conductivity type and being spaced apart from the compensated channel region, as required by claim 13.

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The other references cited by the Examiner have been reviewed, but are not felt to come within the scope of the claims as amended.

In light of the above, Applicant respectfully requests withdrawal of the Examiner's rejections and allowance of claims 1-18. If the Examiner has any questions or other correspondence regarding this application, Applicant requests that the Examiner contact Applicant's attorney at the below listed telephone number and address.

Respectfully submitted,



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